2013 International Workshop on EUVL

Maui, Hawaii, June 10-14, 2013

List of Leading EUVL Technical Challenges

This year, based on the feedback of technical steering committee, we have created a list of leading technical challenges as suggested topics to be addressed by presenters in the 2013 EUVL Workshop. We encourage authors to review this list and choose one of the specific topics for their papers in the area of source, mask, optics, resist and BEUV.

Source

Power scaling for current Sn based DPP and LPP sources
Physics of high power plasma and non-plasma sources (100 W -1000 W)
High brightness EUV sources to support mask metrology
BEUV Sources
Source requirements for high NA scanners for 10 nm and smaller nodes
Source power requirements for 450 mm wafer scanners

Optics and Contamination

High NA optics manufacturing
High NA scanner design
Thermal management for LPP normal incidence collectors
High reflectivity BEUV optics
Source debris management strategy
Carbon contamination and low contamination materials and process
Strategies for optics contamination control

Mask

Strategies for low defect mask blanks
Mask technology to support high NA scanners, including transition to 9 inch masks
Mask defect metrology: New approaches
Mask pellicles
BEUV (6.x nm) masks

Resist

Meeting simultaneous requirements for LER, sensitivity and resolution for EUV resists
Post-processing approaches to reduce LER
Resist materials and process for 1x node
High absorption resists
Resists materials for BEUV (6.x nm)